

## Publikationen

(2011): Nanoscale and Device Level Gate Conduction Variability of High-k Dielectrics-Based Metal-Oxide-Semiconductor Structures. In: IEEE Transactions on Device and Materials Reliability, vol. 11, no. September, pp. 495-501. DOI: 10.1109/TDMR.2011.2161087.

(2011): Reliability and gate conduction variability of HfO<sub>2</sub>-based MOS devices: A combined nanoscale and device level study. In: Microelectronic Engineering, vol. 88, pp. 1334-1337.